



P-CHANNEL ENHANCEMENT MODE MOSFET

Features

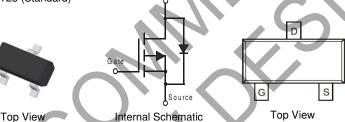
- Low On-Resistance
 - $60m\Omega @ V_{GS} = -4.5V$
 - 90mΩ @ VGS = -2.5V
 - 113mΩ @ VGS = -1.8V •
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMP2305UQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/guality/product-definitions/

Mechanical Data

- Package: SOT23 .
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208(e3)
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)

SOT23 (Standard)



Ordering Information (Note 4)

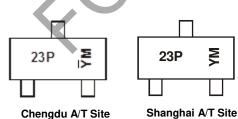
| Part Number | Qualification Package | | Packing | | | |
|---------------|-----------------------|------------------|---------|-------------|--|--|
| Part Nulliber | Quanneation | Package | Qty. | Carrier | | |
| DMP2305UQ-7 | Automotive | SOT23 (Standard) | 3000 | Tape & Reel | | |

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds. 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



23P = Product Type Marking Code YM = Date Code Marking for SAT (Shanghai Assembly/ Test Site) <u>YM</u> = Date Code Marking for CAT (Chengdu Assembly/ Test Site) Y or \overline{Y} = Year (ex: J = 2022) M = Month (ex: 2 = February)

Σ

Date Code Key

| Month | Jan | Feb | Mar | Apr | Mav | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|------|------|------|------|------|------|------|------|------|------|------|------|
| Month | .lan | Feb | Mar | Δnr | May | .lun | .lul | Aua | Sep | Oct | Nov | Dec |
| Code | J | K | L | М | Ν | 0 | Р | R | S | T | U | V |
| Year | 2022 | 2023 | 2024 | 2025 | 2026 | 2027 | 2028 | 2029 | 2030 | 2031 | 2032 | 2033 |



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characte | eristic | | Symbol | Value | Unit |
|-----------------------------------|-----------------|--------------------------|------------------|--------------|------|
| Drain-Source Voltage | | | VDSS | -20 | V |
| Gate-Source Voltage | | | V _{GSS} | ±8 | V |
| Continuous Drain Current (Note 5) | Steady State | TA = +25°C TA = +70°C | lo | -4.2 -3.4 | А |
| Pulsed Drain Current (Note 6) | | | Ідм | -10 | А |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|-----------------------------------------------------------------|------------------|-------------|------|
| Power Dissipation (Note 5) | PD | 1.4 | W |
| Thermal Resistance, Junction to Ambient @T _A = +25°C | R _{0JA} | 90 | °C/W |
| Operating and Storage Temperature Range | TJ, TSTG | -55 to +150 | °C |

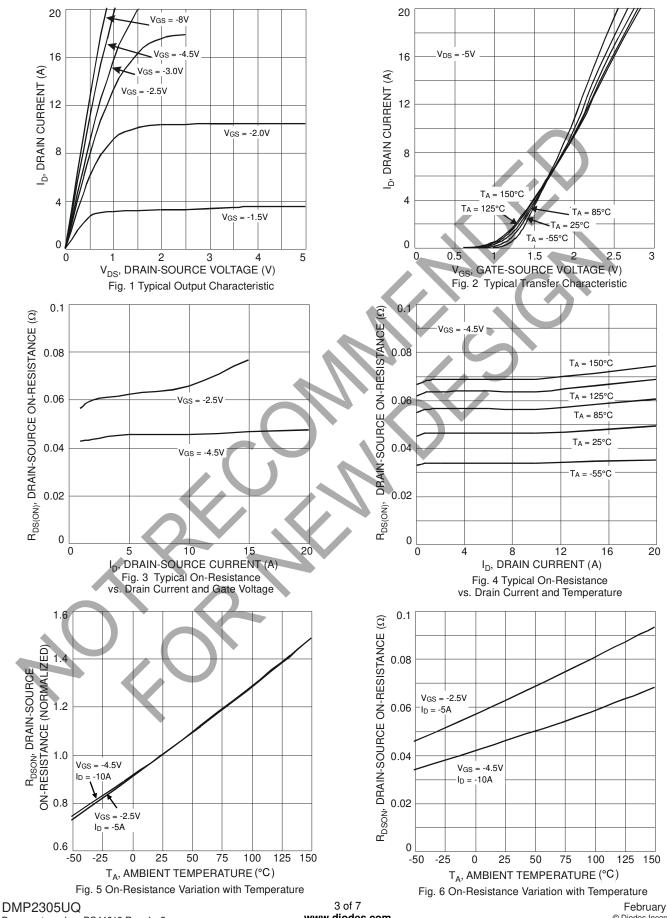
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
|------------------------------------------------------|-----------------|------|------|------|------|----------------------------------------------------------|--|
| OFF CHARACTERISTICS (Note 7) | | | | | | | |
| Drain-Source Breakdown Voltage | | -20 | — | | V | VGS = 0V, ID = -250µA | |
| Zero Gate Voltage Drain Current $T_J = +25^{\circ}C$ | | | | -1.0 | μA | $V_{DS} = -20V, V_{GS} = 0V$ | |
| Gate-Source Leakage | lgss | | | ±100 | nA | $V_{GS} = \pm 8V, V_{DS} = 0V$ | |
| ON CHARACTERISTICS (Note 7) | | | | | | | |
| Gate Threshold Voltage | VGS(TH) | -0.5 | | -0.9 | V | $V_{DS} = V_{GS}$, $I_D = -250 \mu A$ | |
| | | | 45 | 60 | | $V_{GS} = -4.5V, I_{D} = -4.2A$ | |
| Static Drain-Source On-Resistance | RDS(ON) | - | 60 | 90 | mΩ | $V_{GS} = -2.5V, I_{D} = -3.4A$ | |
| | | | 87 | 113 | | V _{GS} = -1.8V, I _D = -2.0A | |
| Forward Transfer Admittance | Y _{FS} | | 9 | _ | S | $V_{DS} = -5V, I_D = -4A$ | |
| DYNAMIC CHARACTERISTICS (Note 8) | | | | | | | |
| Input Capacitance | Ciss | | 727 | _ | pF | | |
| Output Capacitance | Coss | | 69 | _ | pF | V _{DS} = -20V, V _{GS} = 0V, f = 1.0MHz | |
| Reverse Transfer Capacitance | Crss | _ | 64 | _ | pF | | |
| Gate Resistance | Rg | · _ | 23 | _ | Ω | $V_{GS} = 0V, V_{DS} = 0V, f = 1.0MHz$ | |
| SWITCHING CHARACTERISTICS | | 1 | 1 | | | | |
| Total Gate Charge | Qg | | 7.6 | _ | nC | | |
| Gate-Source Charge | Qgs | | 1.4 | _ | nC | $V_{GS} = -4.5V, V_{DS} = -4V, I_D = -3.5A$ | |
| Gate-Drain Charge | Qgd | | 1.2 | _ | nC | | |
| Turn-On Delay Time | td(on) | | 14.0 | _ | ns | | |
| Turn-On Rise Time | t _R | | 13.0 | _ | ns | $V_{DS} = -4V, V_{GS} = -4.5V,$ | |
| Turn-Off Delay Time | td(OFF) | | 53.8 | _ | ns | $R_L = 4\Omega$, $R_G = 6\Omega$, $I_D = -1A$ | |
| Turn-Off Fall Time | t _F | | 23.2 | | ns | | |

Notes:

Device mounted on FR-4 PCB with 2oz. copper and test pulse width t ≤ 10s.
Repetitive rating, pulse width limited by junction temperature.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to production testing.



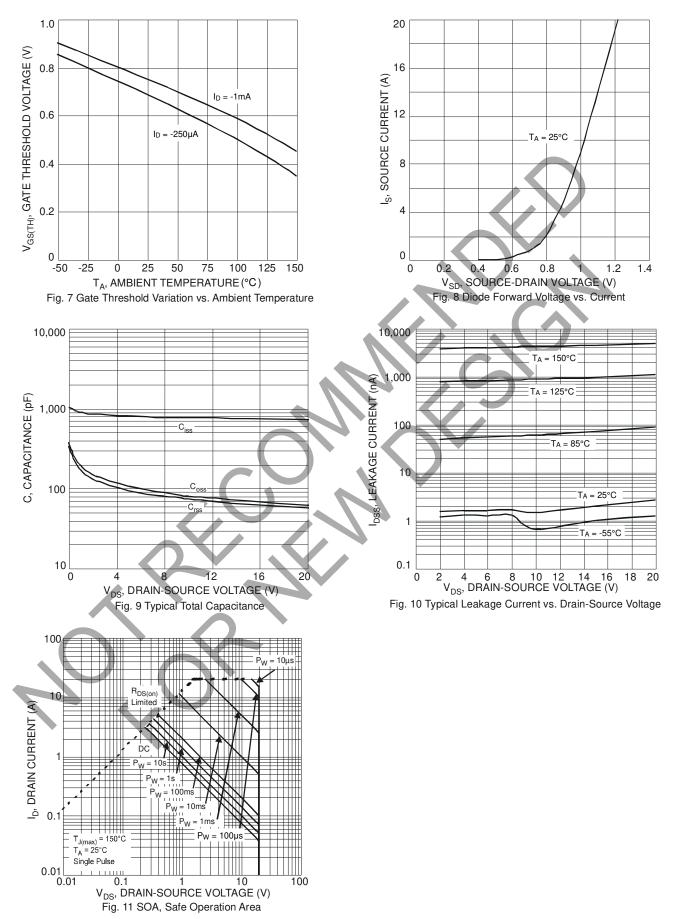


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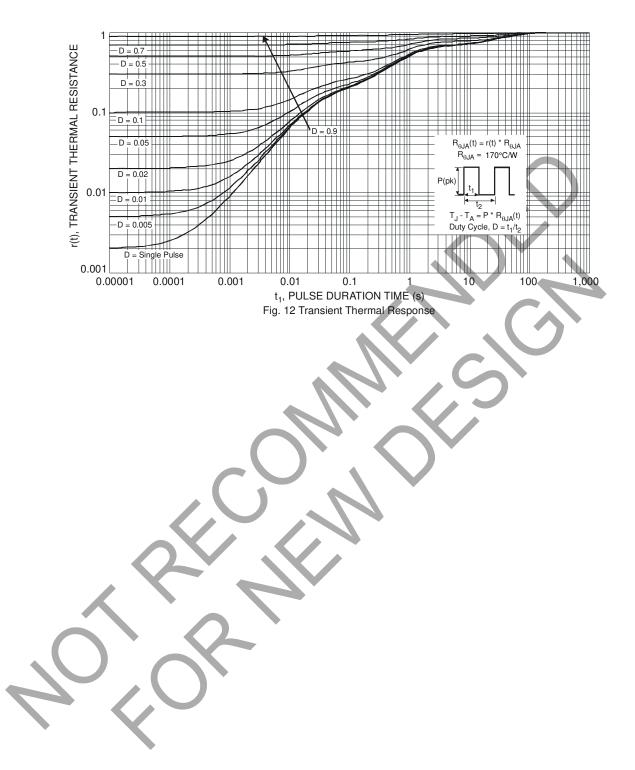
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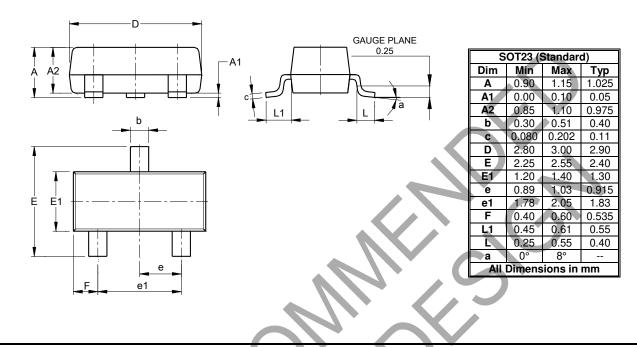






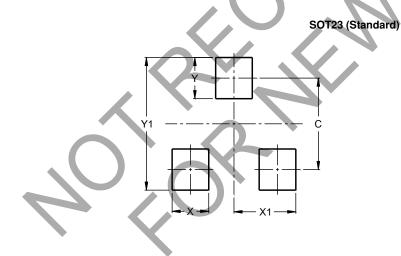
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| С | 2.0 |
| Х | 0.8 |
| X1 | 1.35 |
| Y | 0.9 |
| Y1 | 2.9 |

SOT23 (Standard)



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